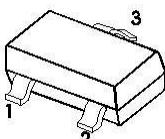


贴片塑封三极管

**SOT-23 Plastic-Encapsulate Transistors**SOT-23

1. BASE  
2. Emitter  
3. Collector

Marking:493

**特征 Features**

与 MMBT593 配对; Complementary to MMBT593

最大功率耗散 250mW; Power Dissipation of 250mW

高稳定性和可靠性, High Stability and High Reliability

**机械数据 Mechanical Data**

封装: SOT-23 封装 SOT-23 Small Outline Plastic Package

环氧树脂 UL 易燃等级 Epoxy UL: 94V-0

安装位置: 任意 Mounting Position: Any

极限值和温度特性(TA = 25 °C 除非另有规定)

**Maximum Ratings & Thermal Characteristics** (Ratings at 25 °C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
Collector-Base Voltage	V <sub>CBO</sub>	120	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter -Base Voltage	V <sub>EBO</sub>	5	V
Collector Current-Continuous	I <sub>C</sub>	1000	mA
Collector Power Dissipation	P <sub>C</sub>	250	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55~+150	°C
Thermal resistance From junction to ambient	R <sub>θJA</sub>	500	°C/W

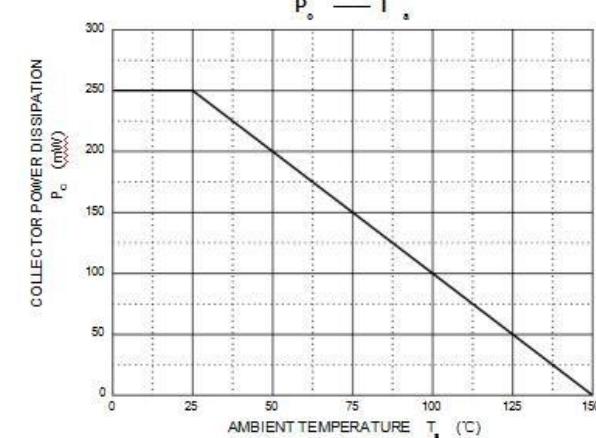
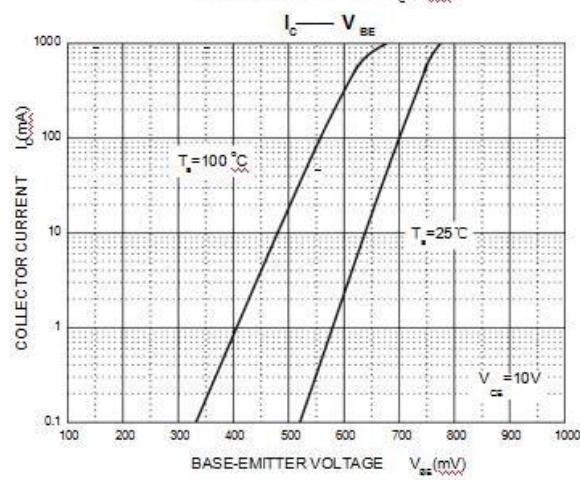
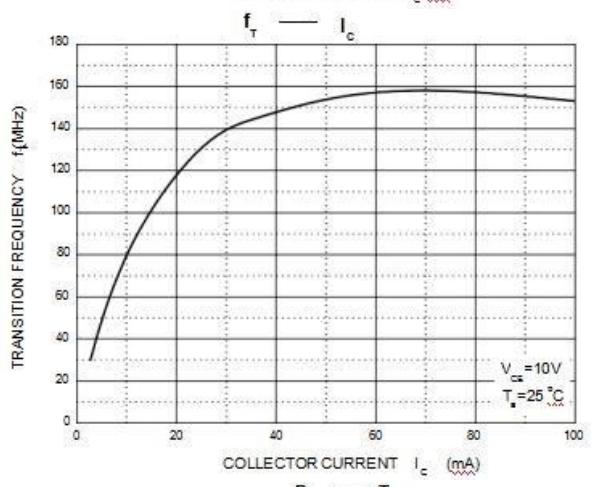
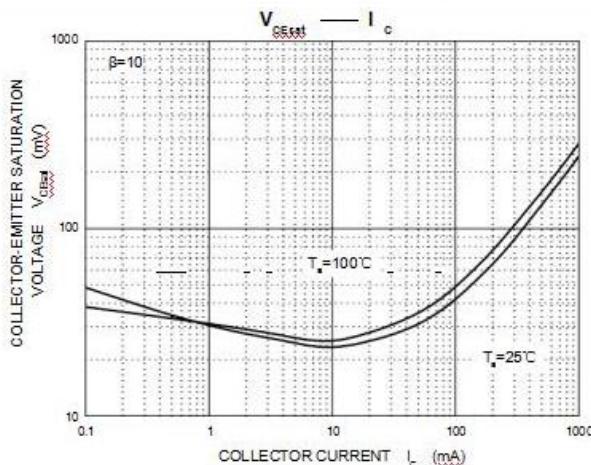
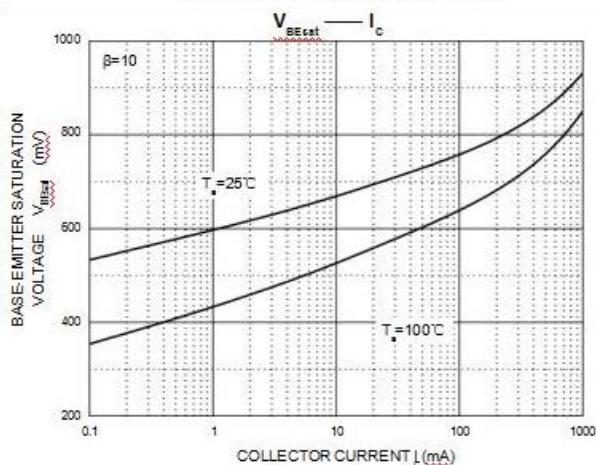
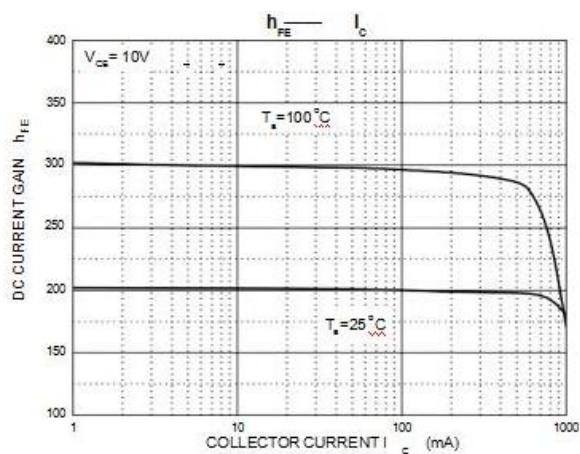
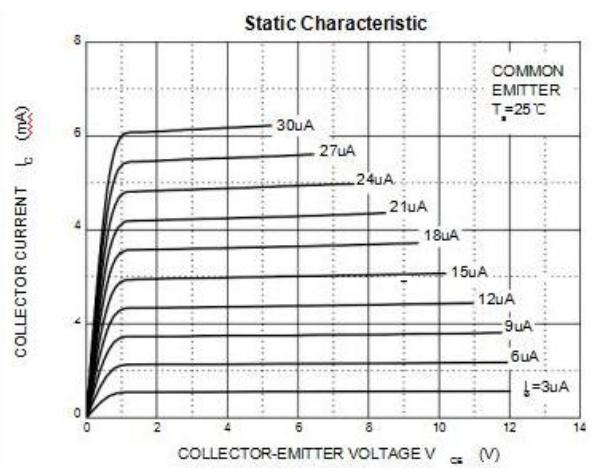
电特性 (TA = 25 °C 除非另有规定)

**Electrical Characteristics** (Ratings at 25 °C ambient temperature unless otherwise specified.)

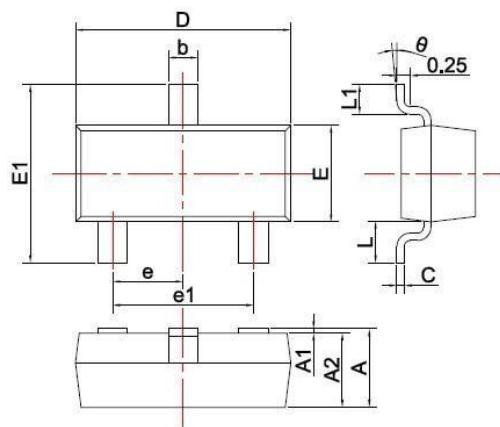
参数 Parameter	符号 Symbols	测试条件 Test Condition	界限 Limits		单位 Unit
			Min	Max	
Collector-base breakdown voltage	V(BR)CBO	IC=100uA, IE=0	120		V
Collector-emitter breakdown voltage	V(BR)CEO	IC=10mA, IB=0	100		V
Emitter-base breakdown voltage	V(BR)EBO	IE=100uA, IC=0	5		V
Collector cut-off current	I <sub>CES</sub>	V <sub>CES</sub> =100V, IE=0		100	nA
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =100V, IE=0		100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, IC=0		100	nA
DC current gain	h <sub>FE</sub> (1)*	V <sub>CE</sub> =10V, IC=1mA	100		
	h <sub>FE</sub> (2)*	V <sub>CE</sub> =10V, IC=250mA	100	300	
	h <sub>FE</sub> (3)*	V <sub>CE</sub> =10V, IC=0.5A	60		
	h <sub>FE</sub> (4)*	V <sub>CE</sub> =10V, IC=1A	20		
Collector-emitter saturation voltage	V <sub>C(E)sat</sub> 1*	IC=500mA, IB=50mA		0.30	V
	V <sub>C(E)sat</sub> 2*	IC=1A, IB=100mA		0.60	V
Base -emitter saturation voltage	V <sub>B(E)sat</sub> *	IC=1A, IB=100mA		1.15	V
Base-emitter voltage	V <sub>BE</sub> *	V <sub>CE</sub> =10V, IC=1A		1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, IC=50mA, f=100MHz	150		
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, IE=0, f=1MHz		10	pF

\*Pulse test: pulse width ≤ 300μs, duty cycle ≤ 2.0%.

## 典型特性曲线 Typical characteristics



## SOT-23 PACKAGE OUTLINE Plastic surface mounted package

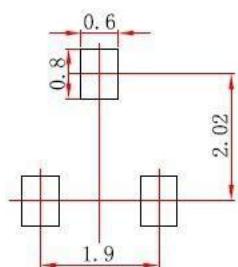


SYMBOL	DIMENSIONS	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
$\theta$	0°	8°

Unit: mm

### 焊盘设计参考Precautions: PCB Design

Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



#### Note:

1. Controlling dimension: In millimeters.
2. General tolerance:  $\pm 0.05$  mm.
3. The pad layout is for reference purposes only.